

CLAIM AMENDMENTS:

Please cancel Claims 10, and amend Claims 1, 4, 7, and 9 as follows:

1. (Currently Amended) A field effect transistor comprising:
a substrate comprising a source region and a drain region;
an insulating layer arranged on the substrate; and
a porous body which has pillar-shaped ~~holes~~ pores arranged on the insulating layer, so that a detected material is introduced in the pores,
wherein ~~the insulating layer is formed between the substrate and the porous body~~ an average pore diameter of the pillar-shaped pores is 50 nm or less.
2. (Cancelled)
3. (Previously Amended) The field-effect transistor according to Claim 1, characterized in that the porous body is composed of an insulating material or a semiconductor material.
4. (Currently Amended) The field-effect transistor according to Claim 3, characterized in that the porous body includes a semiconductor material ~~is a material which uses~~ having silicon, germanium, or silicon and germanium as a main component.
5. (Original) The field-effect transistor according to Claim 3, characterized in that the insulating material is a material which uses silicon oxide as a main component.
6. (Original) The field-effect transistor according to Claim 1, characterized in that average pore diameter of the pillar-shaped pores is 20 nm or less, and mean pore density is 1.5×10^{11} pores/cm² or more.

7. (Currently Amended) The field-effect transistor according to Claim 1, having on surfaces of the pillar-shaped pores a detection material for detecting a specific said detected material.

8. (Original) The field-effect transistor according to Claim 7, characterized in that the detection material is a biomaterial.

9. (Previously Presented) The field-effect transistor according to Claim 6, characterized in that ~~the detection material causes a change of an electric charge state by~~
~~contacting with~~ of the porous body changes when the detected material contacts the porous body.

10.-11. (Cancelled)